

Silicon Flip Chip TVS

Features

- Low leakage current
- Applicable to flip chip package

Structure

- Lateral PNP Bi-directional Structure

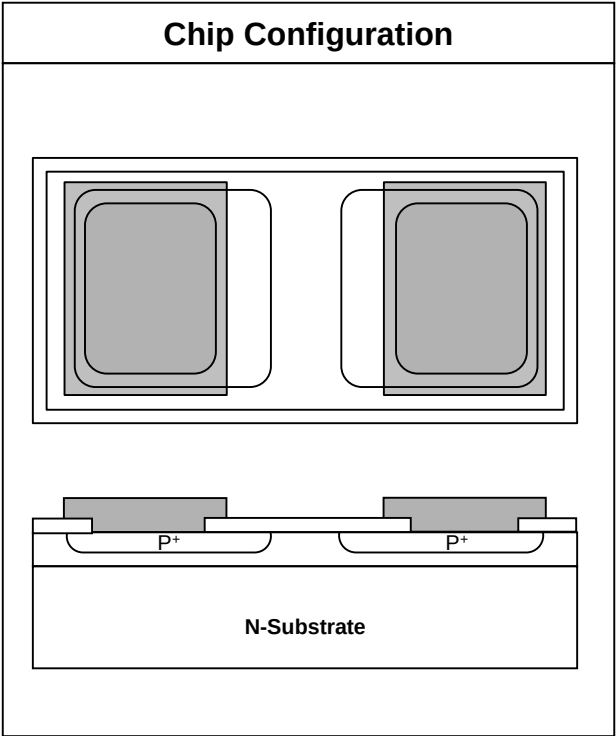
- Electrode

Structure: Dual pad

Pad metal: AuSn

Size

- Chip size : 415(±20) μm x 210(±20) μm
- Thickness : 100(±20) μm
- Pad size : 90(±5) μm x 120(±5) μm
- Pad space : 113 μm



Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Maximum Rating	Unit
Power Dissipation	P _d	100	mW
Junction Temperature	T _j	150	°C

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V _F	I _F = 10 mA	6.0	-	9.0	V
Forward Leakage Current	I _F	V _F = 4 V	-	-	0.1	μA
Reverse Voltage	V _R	I _R = 10 mA	6.0	-	9.0	V
Reverse Leakage Current	I _R	V _R = 4 V	-	-	0.1	μA

Equivalent Circuit

